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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.
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1765/119

EXAMINER

09/27/94

ART UNIT

PAPER NUMBER

1765

DATE MAILED:

03/14/01

Please find below and/or attached an Office communication concerning this application or proceeding.

Commissioner of Patents and Trademarks

Office Action Summary

Application No.

09/405,945

Applicant(s)

JIN ET AL.

Examiner

Lynette T. Umez-Eronini

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-- The MAILING DATE of this communication appears on the cover sheet with the correspondence address --

Period for Reply

A SHORTENED STATUTORY PERIOD FOR REPLY IS SET TO EXPIRE 3 MONTH(S) FROM THE MAILING DATE OF THIS COMMUNICATION.

- Extensions of time may be available under the provisions of 37 CFR 1.136 (a). In no event, however, may a reply be timely filed after SIX (6) MONTHS from the mailing date of this communication.
- If the period for reply specified above is less than thirty (30) days, a reply within the statutory minimum of thirty (30) days will be considered timely.
- If NO period for reply is specified above, the maximum statutory period will apply and will expire SIX (6) MONTHS from the mailing date of this communication.
- Failure to reply within the set or extended period for reply will, by statute, cause the application to become ABANDONED (35 U.S.C. § 133).

Status

- 1) ☐ Responsive to communication(s) filed on ____.
- 2a) ☐ This action is **FINAL**. 2b) ☒ This action is non-final.
- 3) ☐ Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under *Ex parte Quayle*, 1935 C.D. 11, 453 O.G. 213.

Disposition of Claims

- 4) ☒ Claim(s) 1-14 and 16-19 is/are pending in the application.
- 4a) Of the above claim(s) ____ is/are withdrawn from consideration.
- 5) ☐ Claim(s) ____ is/are allowed.
- 6) ☐ Claim(s) ____ is/are rejected.
- 7) ☐ Claim(s) ____ is/are objected to.
- 8) ☐ Claims ____ are subject to restriction and/or election requirement.

Application Papers

- 9) ☐ The specification is objected to by the Examiner.
- 10) ☐ The drawing(s) filed on ____ is/are objected to by the Examiner.
- 11) ☐ The proposed drawing correction filed on ____ is: a) ☐ approved b) ☐ disapproved.
- 12) ☐ The oath or declaration is objected to by the Examiner.

Priority under 35 U.S.C. § 119

- 13) ☐ Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d).
- a) ☐ All b) ☐ Some * c) ☐ None of the CERTIFIED copies of the priority documents have been:
1. ☐ received.
2. ☐ received in Application No. (Series Code / Serial Number) ____.
3. ☐ received in this National Stage application from the International Bureau (PCT Rule 17.2(a)).
- * See the attached detailed Office action for a list of the certified copies not received.
- 14) ☐ Acknowledgement is made of a claim for domestic priority under 35 U.S.C. & 119(e).

Attachment(s)

- 14) ☒ Notice of References Cited (PTO-892)
- 15) ☐ Notice of Draftsperson's Patent Drawing Review (PTO-948)
- 16) ☐ Information Disclosure Statement(s) (PTO-1449) Paper No(s) ____
- 17) ☐ Interview Summary (PTO-413) Paper No(s). ____
- 18) ☐ Notice of Informal Patent Application (PTO-152)
- 19) ☐ Other:

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DETAILED ACTION

Claim Rejections - 35 USC § 103

1. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negated by the manner in which the invention was made.

2. Claim 1 is rejected under 35 U.S.C. 103(a) as being unpatentable over Hsue (US 5,378,654) in view of Chang et al. (US 5,893,740).

Hsue teaches in the prior art, a conventional method of forming a self-aligned contact (SAC) on a MOSFET device (column 1, lines 6, 7, 25-27, and Figure 1A-1F). The method comprises forming silicon dioxide **21** (insulating layer) over polysilicon gate structures **15** (transistor gate) and substrate **10** (Figure 1A), forming silicon oxide spacers **18** (insulating sidewalls) on the polysilicon gate structures **15** (Figures 1C-1F), forming a SAC contact opening in the silicon oxide layer **21**, and etching a portion of the silicon dioxide layer **21** that is exposed through a mask **22** to open a portion of the surface of N+ doped region (column 2, lines 14-19). These steps do not include the formation of an etch stop layer over the insulating layer (silicon dioxide **21**), which reads on, without forming a contact hole etch stop liner.

Hsue differs in failing to teach a transistor have a gate length of less than 0.2 microns, **in claim 1**.

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Chang does not teach using the channel field effect transistor in forming a self aligned contact hole, however, Chang uses a gate electrode of 0.1 μm in length to make up a transistor (column 4, lines 55 and 56). Hence, Chang's gate electrode is the same as a transistor gate and reads on a transistor gate having a gate length less than 0.2 microns.

It would have been obvious to one having ordinary skill in the art at the time of the claimed invention to modify Hsue by using a transistor with a gate length of less than 0.2 microns as taught by Chang for the purpose of obtaining the claimed invention.

3. Claims 2-11 are rejected under 35 U.S.C. 103(a) as being unpatentable over Hsue (US 5,378,654) in view of Chang et al. (US 5,893,740) as applied to claim 1 above, and further in view of Nulty et al. (US 5,468,342).

Hsue differs in failing to specify processing parameters as recited **in claims 3-11**.

It would have been obvious to one having ordinary skill in the art at the time of the claimed invention to employ any of a variety of processing variables including those claimed by the applicant. They are well-known variables in the etching art and known to affect both the rate and quality of the etching process. The selection of a particular value would be optimized by conducting routine experimentation for the purpose of forming a contact hole.

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Hsue in view of Chang differs in failing to teach forming a contact hole includes reactive plasma etching through a first insulating layer comprising non-densified doped silicon dioxide, **in claim 2**.

In the art of fabricating semiconductor devices, Nulty teaches forming contact openings in an oxide layer (column 4, lines 21 and 22). The oxide layer be undoped or doped, for example BPSG (borophosphosilicate glass) (column 1, lines 17-25). An opening is formed through the BPSG layer by carrying out the etching in a reactive ion etching system (column 1, lines 14-25 and column 6, lines 15-20 and 54-57, and column 7, lines 4-6 and 17-19). The BPSG layer is deposited by CVD (column 6, lines 12-15), that suggests it is a non-densified doped silicon dioxide layer.

It would have been obvious to one having ordinary skill in the art at the time of the claimed invention to modify Hsue in view of Chang by forming a contact hole that includes reactive plasma etching through a first insulating layer comprising non-densified doped silicon dioxide as taught by Nulty for the purpose of providing a region whereby contact is made on a semiconductor substrate.

4. Claims 12-14 and 16 are rejected under 35 U.S.C. 103(a) as being unpatentable over Hsue (US 5,378,654) in view of Chang et al. (US 5,893,740).

Hsue differs in failing to teach etching a first insulating layer comprising doped silicon dioxide, **in claim 12**.

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It would have been obvious to one having ordinary skill in the art at the time of the claimed invention to use a conventional insulating layer such as silicon dioxide for the purpose of forming a contact region in a semiconductor substrate.

Hsue further differs in failing to teach an etch selectivity between the first insulating layer and the sidewall that is greater than 10:1 and an etch selectivity between the first insulating layer and the substrate is greater than 100:1, **in claim 12**.

Using the method, oxide insulating layer and insulating sidewall materials of Hsue, which are the same as those of the claimed invention would inherently result obtaining the same etch selectivities as claimed in the present invention.

5. Claims 17-19 are rejected under 35 U.S.C. 103(a) as being unpatentable over Hsue (US 5,378,654) in view of Chang et al. (US 5,893,740) and further in view of Avinzino et al. (US No. 5,776,834).

Hsue differs in failing to teach

forming a hard mask comprising undoped silicate glass over an insulating layer comprising doped silicon dioxide and the hard mask having openings over a contact hole location, **in claim 17**.

In the art of etching semiconductor material, it would have been obvious to one having ordinary skill in the art at the time of the claimed invention to use conventional materials such as undoped silicon dioxide and doped silicon dioxide respectively, as a

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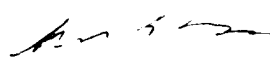
hard etch mask and first insulating layer for the purpose of forming a contact region in a semiconductor substrate.

Hsue differs in view of Chang in failing to teach forming a contact hole wherein the conducting structures are separated from one another by less than 0.4 microns, **in claims 17 and 18.**

Avanzino teaches a pair of conductive lines having a gap of about 0.5 microns or less (Abstract) which reads on conducting structures are separated from one another by less than 0.4 microns.

It would have been obvious to one having ordinary skill in the art to modify Hsue in view of Chang by using conductive lines that are less than 0.5 microns or less as taught by Avanzino for the purpose of obtaining the claimed invention.

6. Any inquiry concerning this communication or earlier communications from the examiner should be directed to Lynette T. Umez-Eronini whose telephone number is 703-306-9074.



ltue
March 12, 2001